PROJECTED RANGE STATISTICS

Flexibility. Expertise. Speed. Everything you need at one implant foundry.



- The following graphs are based on tables generated by SRIM 2013
- SRIM is a software package originally written at IBM Research under the direction of J. F. Ziegler and J. P. Biersack
- It is currently available at no cost for noncommercial use at www.SRIM.org
- The graphs are provided for use by any and all ion implant users
- The graphs provide Projected Range (Rp) and Straggle ($\Delta Rp)$ for
 - Antimony
 - Arsenic
 - Boron
 - Phosphorus

- There are 4 sets of graphs for the following implant target materials
 - Silicon
 - Silicon Dioxide
 - Silicon Nitride
 - Resist (AZ 111)
- Each set of graphs consist of 2, one for singly charge ions and one for multiply charge ions
- In addition, there is a set of graphs recommending a minimum resist thickness
- The recommendations are based on Rp + 5 * Δ Rp.
- Thicker resist may be needed for high doses that cause resist shrinkage





Projected Range Statistics into Silicon ref SRIM 2013



Projected Range Statistics into Silicon ref SRIM 2013





Projected Range Statistics into Oxide ref SRIM 2013



Projected Range Statistics into Oxide ref SRIM 2013





Projected Range Statistics into Nitride ref SRIM 2013



Projected Range Statistics into Nitride ref SRIM 2013





Projected Range Statistics into AZ-111 Resist ref SRIM 2013



Projected Range Statistics into AZ-111 Resist ref SRIM 2013





Projected Range + 5 * Statistics -- Recommended Resist Thickness ref SRIM 2013



Projected Range + 5 * Statistics -- Recommended Resist Thickness ref SRIM 2013

• Based on SRIM 2013 generated tables



sales@ii-vi.com www.ii-vi.com